isc P-Channel MOSFET Transistor SPP80P06P，ISPP80P06P

• FEATURES

- Static drain-source on-resistance:
  R_{DS}(on)≤0.023Ω
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

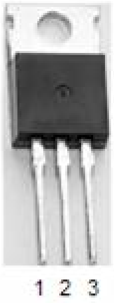
- 175℃ operating temperature
- Avalanche rated
- dv/dt rated

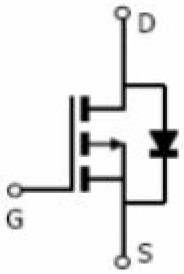
• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	-80	A
I_{DM}	Drain Current-Single Pulsed	-320	A
P_D	Total Dissipation @T_C=25℃	340	W
T_j	Max. Operating Junction Temperature	175	℃
T_{stg}	Storage Temperature	-55~175	℃

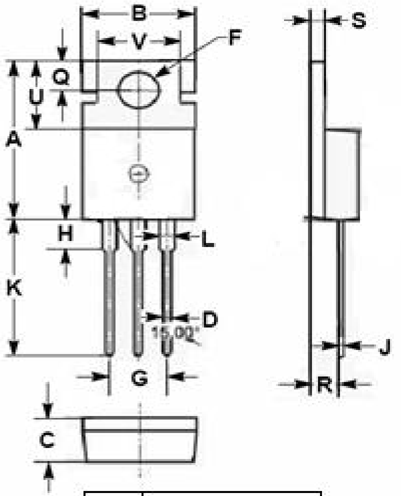
• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	0.4	℃/W
Rth(j-a)	Channel-to-ambient thermal resistance	62	℃/W





pin 1, Gate
2, Drain
3, Source
TO-220C package



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2. 68	2.90
J	0.44	0.60
K	13. 00	13.40
L	1.10	1. 45
Q	2.70	2.90
R	2. 30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= -250μA	-60			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D= -5.5mA	-2.1		-4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= -10V; I_D= -64A			0.023	Ω
I_{GSS}	Gate-Source Leakage Current	V_{GS}= -20V; V_{DS}= 0V			-100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= -60V; V_{GS}= 0V			-1	μA
V_{SD}	Diode forward voltage	I_F= -15A; V_{GS} = 0V			-1.35	V